General Purpose Transistors

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847 BC848	V _{CEO}	65 45 30	٧
Collector-Base Voltage BC846 BC847 BC848	V _{CBO}	80 50 30	V
Emitter-Base Voltage BC846 BC847 BC848	V _{EBO}	6.0 6.0 5.0	V
Collector Current – Continuous	Ic	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

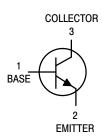
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C	P _D	200	mW
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	620	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.



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SC-70/SOT-323 CASE 419 STYLE 3

MARKING DIAGRAM



XX = Specific Device Code

M = Month Code

= Pb-Free Package

(Note: Microdot may be in either location)

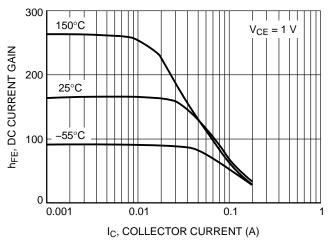
ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 12 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	BC846 Series BC847 Series BC848 Series	V _{(BR)CEO}	65 45 30	- - -	- - -	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A, V_{EB} = 0$)	BC846 Series BC847 Series BC848 Series	V _{(BR)CES}	80 50 30	- - -	- - -	٧
Collector – Base Breakdown Voltage ($I_C = 10 \mu A$)	BC846 Series BC847 Series BC848 Series	V _{(BR)CBO}	80 50 30	- - -	- - -	٧
Emitter-Base Breakdown Voltage (I _E = 1.0 μA)	BC846 Series BC847 Series BC848 Series	V _{(BR)EBO}	6.0 6.0 5.0	- - -	- - -	V
Collector Cutoff Current (V _{CB} = 30 V)	(V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	_ _	- -	15 5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	h _{FE}	- - -	90 150 270	- - -	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C		110 200 420	180 290 520	220 450 800	
Collector – Emitter Saturation Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.00$) ($I_C = 100 \text{ mA}$, $I_B = 0.00$)		V _{CE(sat)}	- -	- -	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 (I_C = 100 mA, I_B = 5.		V _{BE(sat)}	_ _	0.7 0.9	- -	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)		V _{BE(on)}	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 Vdc, f = 100 MHz)		f _T	100	_	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	-	_	4.5	pF
Noise Figure ($I_C = 0.2 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 2.0 \text{ kg}$	2, f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB

BC846A, BC847A, BC848A



300 150°C VCE = 5 V VCE = 5 V 25°C 25°C 0 0.001 0.01 0.1 I_C, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain vs. Collector Current

Figure 2. DC Current Gain vs. Collector Current

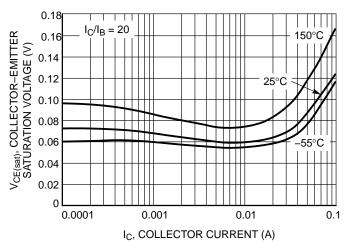
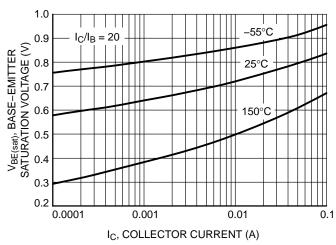
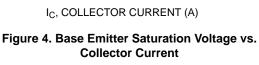


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current





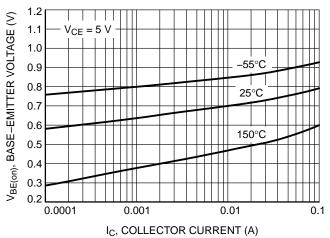


Figure 5. Base Emitter Voltage vs. Collector Current

BC846A, BC847A, BC848A

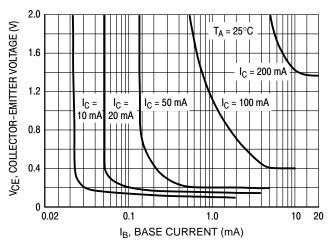


Figure 6. Collector Saturation Region

Figure 7. Base-Emitter Temperature Coefficient

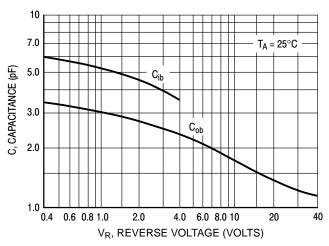


Figure 8. Capacitances

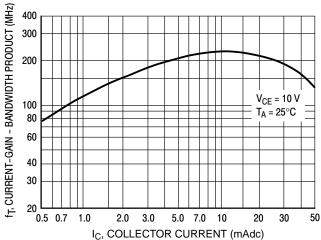


Figure 9. Current-Gain - Bandwidth Product

BC846B

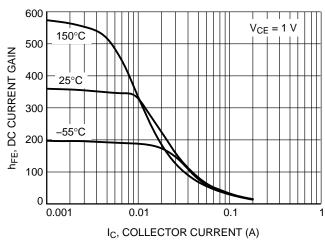


Figure 10. DC Current Gain vs. Collector Current

Figure 11. DC Current Gain vs. Collector Current

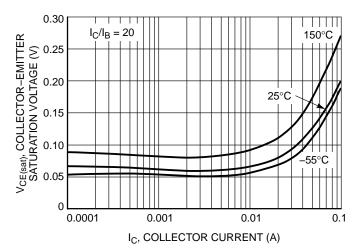
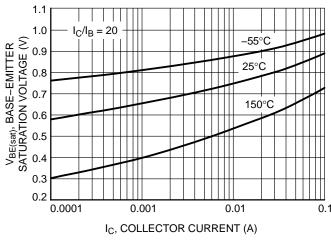


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current



0.1 × vs.

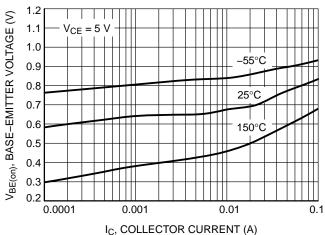
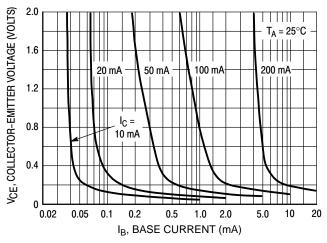


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

Figure 14. Base Emitter Voltage vs. Collector Current

BC846B



 $\theta_{\mbox{\scriptsize VB}}$ TEMPERATURE COEFFICIENT (mV/ $^{\circ}\mbox{\scriptsize C}$ 1.8 θ_{VB} for V_{BE} -55°C to 125°C 2.2 2.6 0.2 2.0 10 50 100 200 0.5 1.0 5.0 I_C, COLLECTOR CURRENT (mA)

Figure 15. Collector Saturation Region

Figure 16. Base-Emitter Temperature Coefficient

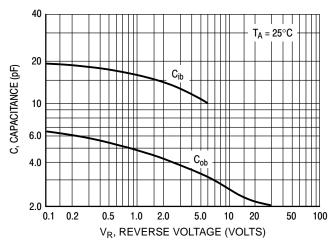


Figure 17. Capacitance

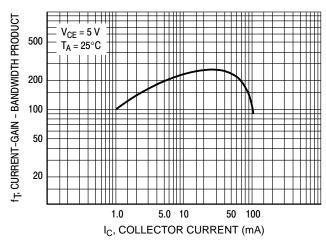
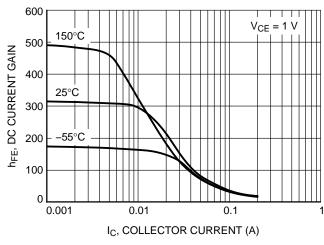


Figure 18. Current-Gain - Bandwidth Product

BC847B, BC848B



600 150°C 150°C 400 25°C 25°C 100 0 0.001 0.01 0.1

Figure 19. DC Current Gain vs. Collector Current

Figure 20. DC Current Gain vs. Collector Current

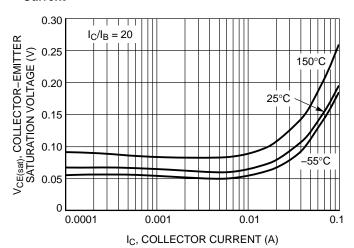
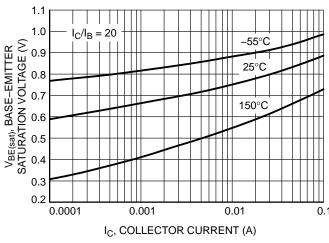


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current





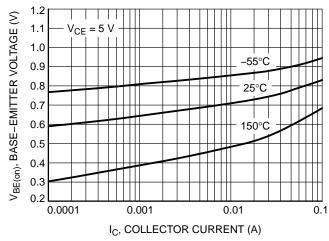
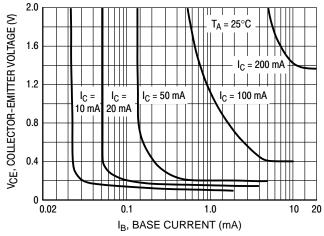


Figure 23. Base Emitter Voltage vs. Collector Current

BC847B, BC848B

1.2

400 300



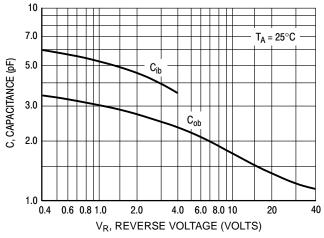
θ√B, TEMPERATURE COEFFICIENT (mV/°C) 1.6 2.0 2.4 2.8 0.2 1.0 10 I_C, COLLECTOR CURRENT (mA)

55°C to +125°C

Figure 24. Collector Saturation Region

Figure 25. Base-Emitter Temperature Coefficient

100



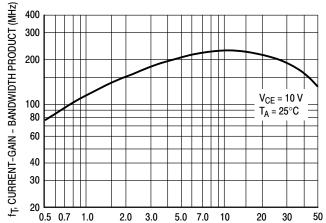
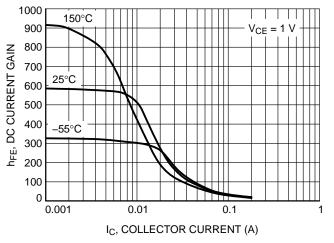


Figure 26. Capacitances

I_C, COLLECTOR CURRENT (mAdc) Figure 27. Current-Gain - Bandwidth Product

BC847C, BC848C



1000 900 150°C 800 hFE, DC CURRENT GAIN 700 600 25°C 500 400 –55°C 300 200 100 0.001 0.01 0.1 I_C, COLLECTOR CURRENT (A)

Figure 28. DC Current Gain vs. Collector Current

Figure 29. DC Current Gain vs. Collector Current

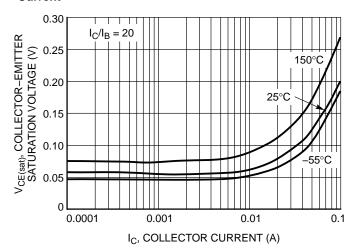
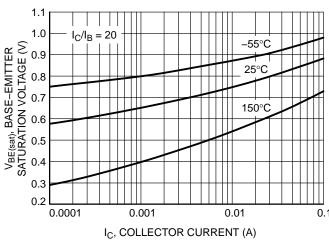


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

1.2



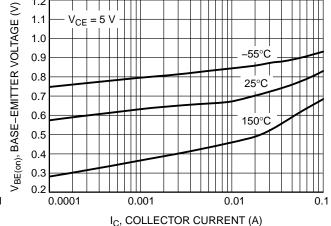


Figure 31. Base Emitter Saturation Voltage vs. **Collector Current**

Figure 32. Base Emitter Voltage vs. Collector Current

BC847C, BC848C

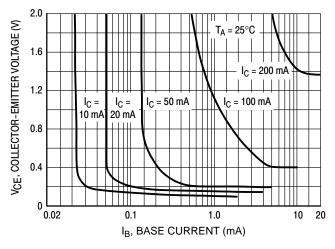
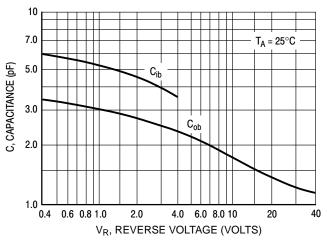


Figure 33. Collector Saturation Region

Figure 34. Base–Emitter Temperature Coefficient





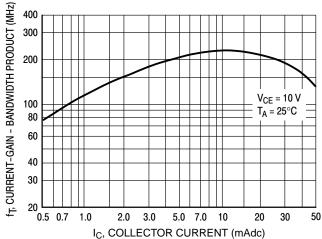


Figure 36. Current-Gain - Bandwidth Product

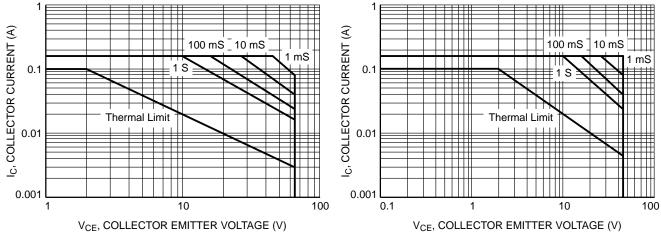
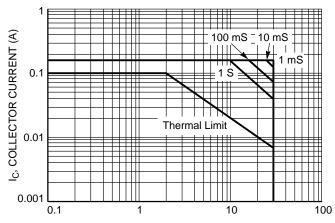


Figure 37. Safe Operating Area for BC846A, BC846B

Figure 38. Safe Operating Area for BC847A, BC847B, BC847C



 V_{CE} , COLLECTOR EMITTER VOLTAGE (V)

Figure 39. Safe Operating Area for BC848A, BC848B, BC848C

DEVICE ORDERING AND SPECIFIC MARKING INFORMATION

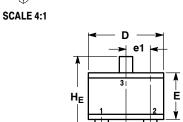
Device	Specific Marking Code	Package	Shipping [†]	
BC846BWT1G	1B	SC-70 (SOT-323) (Pb-Free)	3,000 / Tape & Reel	
SBC846BWT1G*	ID		3,000 / Tape & Neel	
BC847AWT1G	1E		2 000 / Tone & Book	
SBC847AWT1G*	15		3,000 / Tape & Reel	
BC847BWT1G	1F		3,000 / Tape & Reel	
SBC847BWT1G*	IF			
BC847CWT1G	1G		2 000 / Topo & Book	
SBC847CWT1G*	10		3,000 / Tape & Reel	
BC847CWT3G	1G		10,000 / Tape & Reel	
SBC847CWT3G*	10			
BC848BWT1G	1K			
NSVBC848BWT1G*	I I K		3,000 / Tape & Reel	
BC848CWT1G	1L			

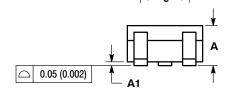
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

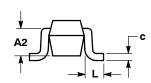


SC-70 (SOT-323) CASE 419-04 ISSUE N

DATE 11 NOV 2008





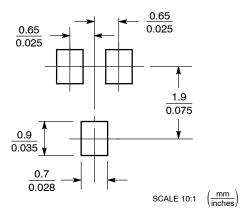


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF 0.028 REF					
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BSC	;
Ĺ	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM



XX = Specific Device Code Μ = Date Code = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	SOURCE	2. CATHODE	2. ANODE	CATHODE
COLLECTOR	COLLECTOR	3. DRAIN	CATHODE-ANODE	3. ANODE-CATHODE	CATHODE

OCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1

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